



ON Semiconductor®

FQP27P06

P-Channel QFET® MOSFET

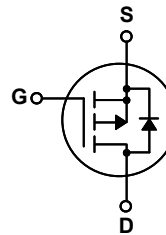
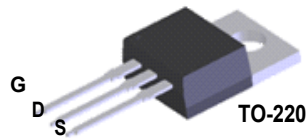
- 60 V, - 27 A, 70 mΩ

Description

This P-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- - 27 A, - 60 V, $R_{DS(on)} = 70 \text{ m}\Omega$ (Max.) @ $V_{GS} = - 10 \text{ V}$, $I_D = - 13.5 \text{ A}$
- Low Gate Charge (Typ. 33 nC)
- Low C_{rss} (Typ. 120 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQP27P06	Unit
V_{DSS}	Drain-Source Voltage	-60	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	-27
		- Continuous ($T_C = 100^\circ\text{C}$)	-19.1
I_{DM}	Drain Current - Pulsed (Note 1)	-108	A
V_{GSS}	Gate-Source Voltage	± 25	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	560	mJ
I_{AR}	Avalanche Current (Note 1)	-27	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	12	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-7.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	120	W
		- Derate above 25°C	0.8
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQP27P06	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.25	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	$^\circ\text{C}/\text{W}$

FQP27P06 P-Channel QFET® MOSFET

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-60	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C	--	-0.06	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$	--	--	-1	μA
		$V_{DS} = -48\text{ V}, T_C = 150^\circ\text{C}$	--	--	-10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-2.0	--	-4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -13.5\text{ A}$	--	0.055	0.07	Ω
g_{FS}	Forward Transconductance	$V_{DS} = -30\text{ V}, I_D = -13.5\text{ A}$	--	12.4	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1100	1400	pF
C_{oss}	Output Capacitance		--	510	660	pF
C_{riss}	Reverse Transfer Capacitance		--	120	155	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -30\text{ V}, I_D = -13.5\text{ A},$ $R_G = 25\ \Omega$	--	18	45	ns
t_r	Turn-On Rise Time		--	185	380	ns
$t_{d(off)}$	Turn-Off Delay Time		--	30	70	ns
t_f	Turn-Off Fall Time		(Note 4)	--	90	190
Q_g	Total Gate Charge	$V_{DS} = -48\text{ V}, I_D = -27\text{ A},$ $V_{GS} = -10\text{ V}$	--	33	43	nC
Q_{gs}	Gate-Source Charge		--	6.8	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4)	--	18	--
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	-27	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	-108	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -27\text{ A}$	--	--	-4.0	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = -27\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	105	--	ns
Q_{rr}	Reverse Recovery Charge		--	0.41	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 0.9\text{ mH}, I_{AS} = -27\text{ A}, V_{DD} = -25\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq -27\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature

Typical Characteristics

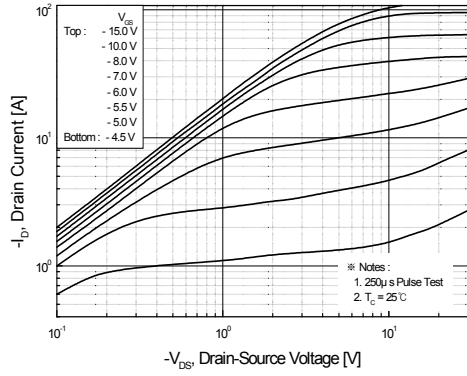


Figure 1. On-Region Characteristics

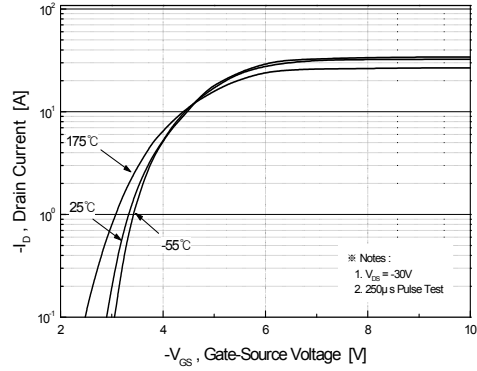


Figure 2. Transfer Characteristics

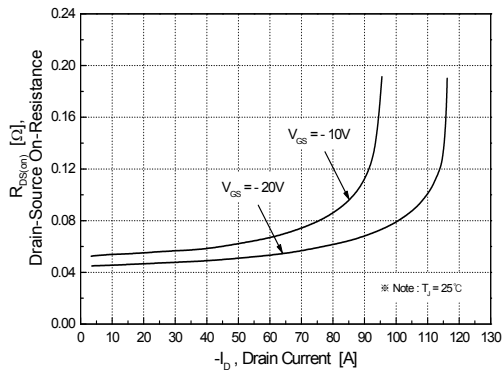


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

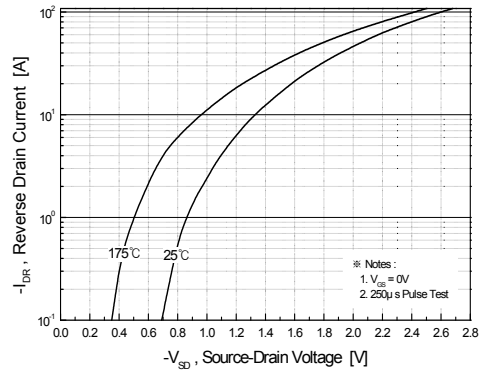


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

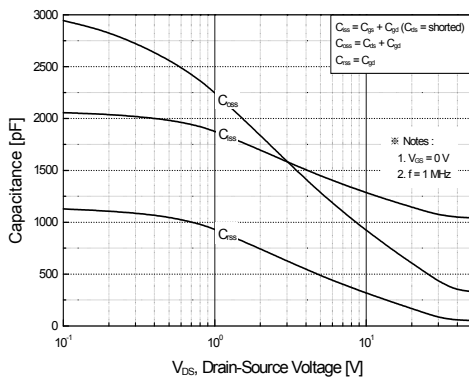


Figure 5. Capacitance Characteristics

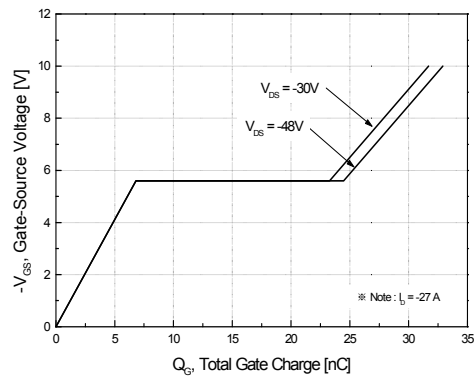


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

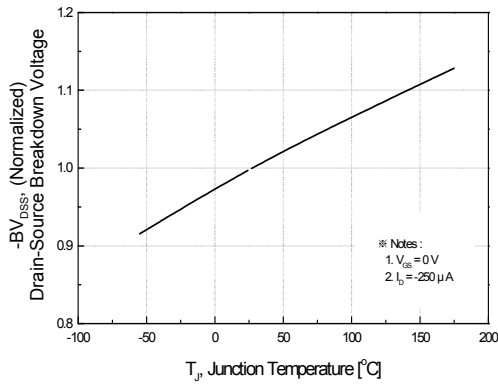


Figure 7. Breakdown Voltage Variation vs. Temperature

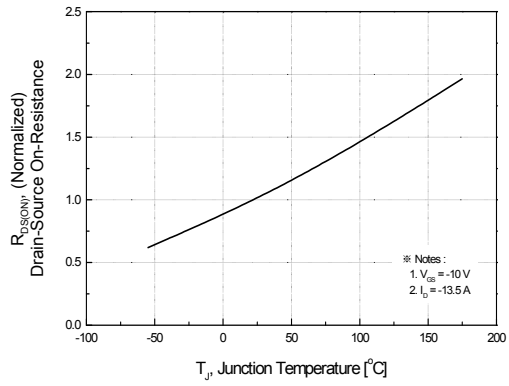


Figure 8. On-Resistance Variation vs. Temperature

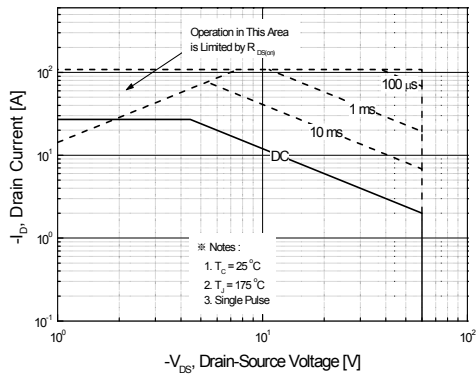


Figure 9. Maximum Safe Operating Area

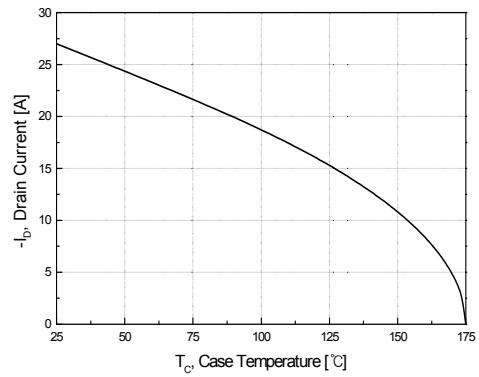


Figure 10. Maximum Drain Current vs. Case Temperature

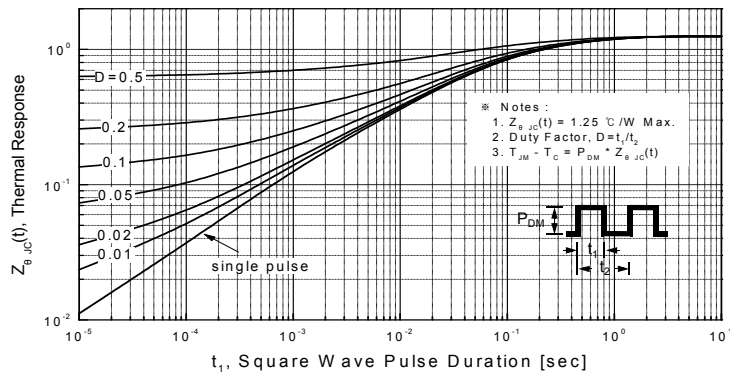
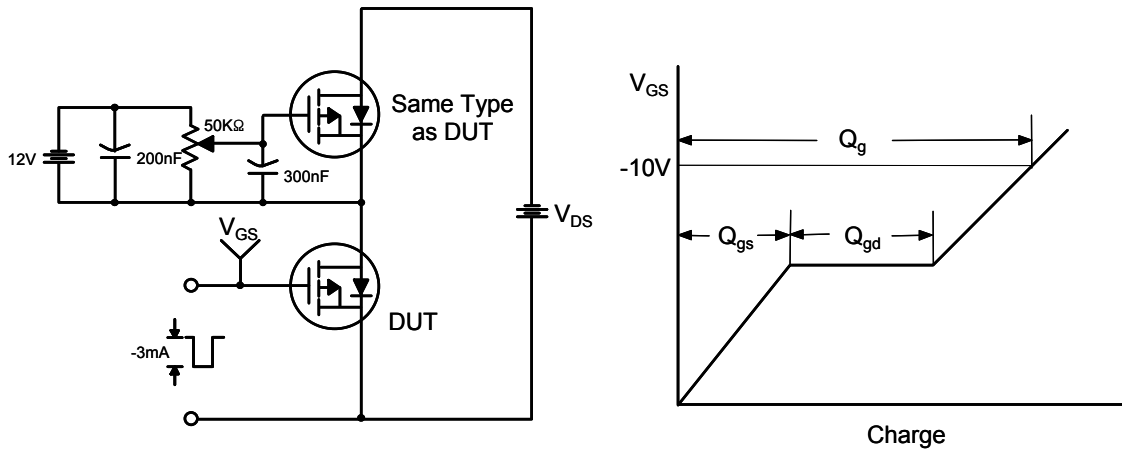
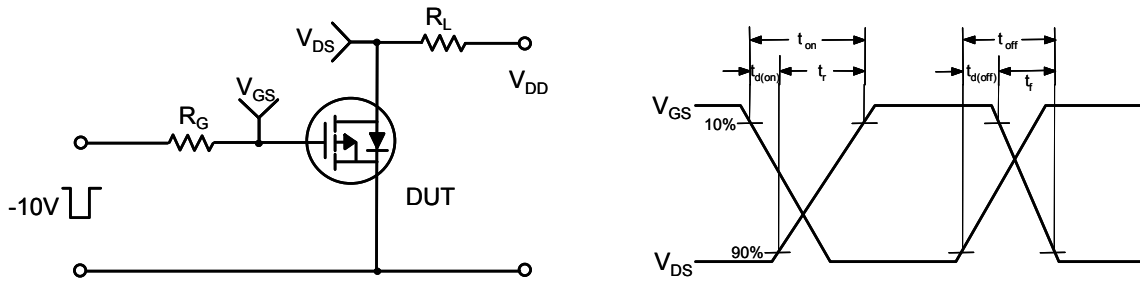


Figure 11. Transient Thermal Response Curve

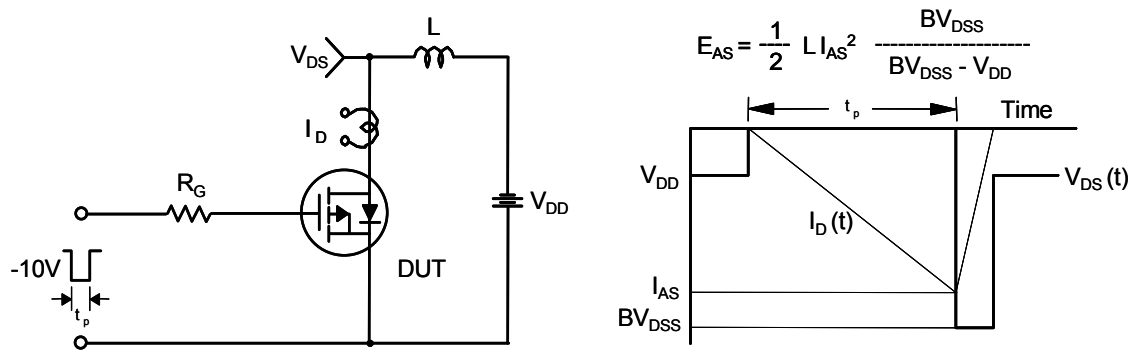
Gate Charge Test Circuit & Waveform



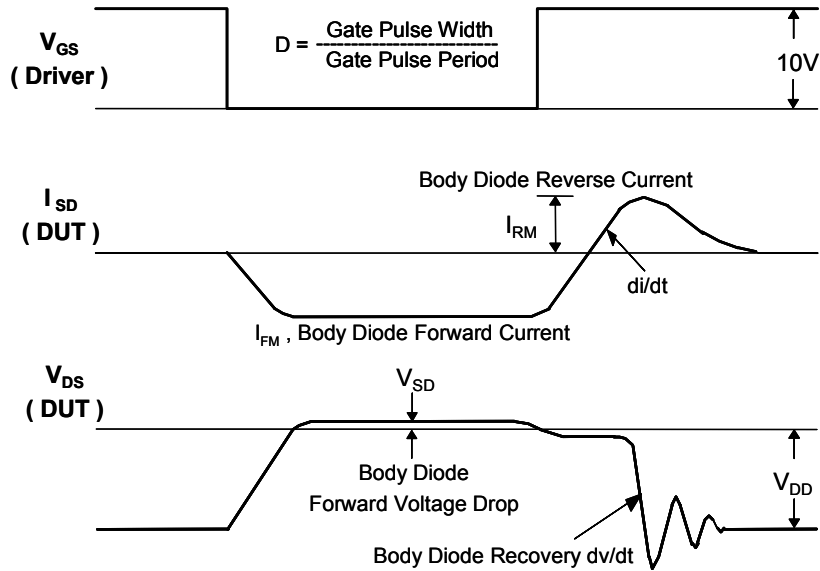
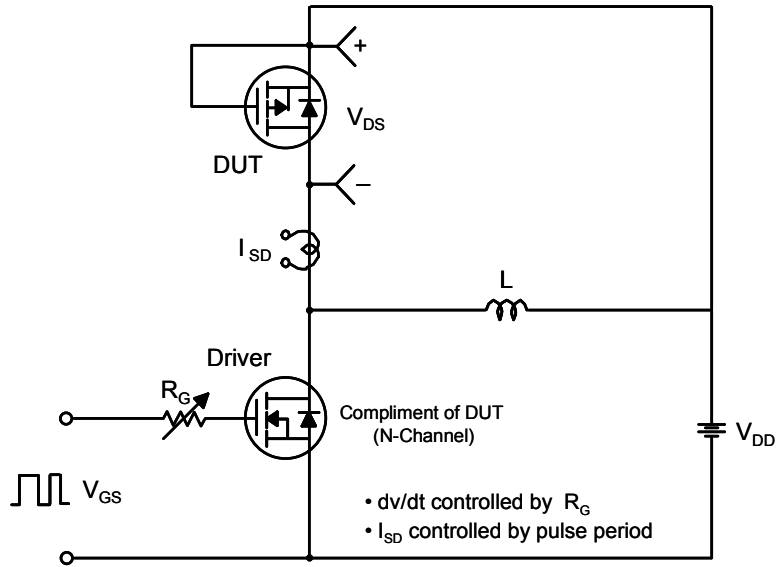
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

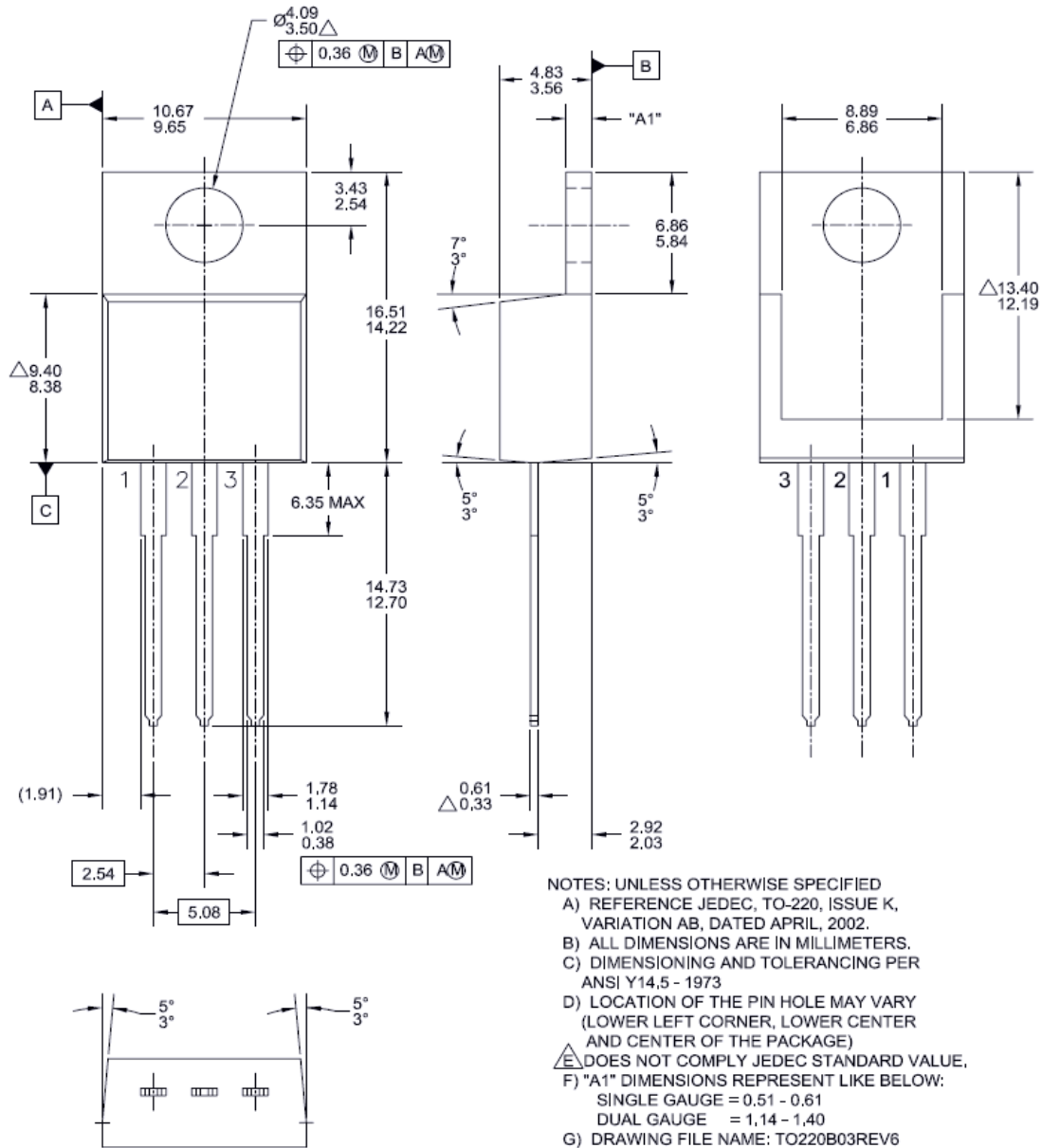


Peak Diode Recovery dv/dt Test Circuit & Waveforms




Package Dimensions

TO-220



FQP27P06 P-Channel QFET[®] MOSFET

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